

IN THE CLAIMS:

1-2. (Canceled)

3. (Currently Amended) A semiconductor device, comprising:

a substrate having an insulating surface;

a semiconductor film over the substrate;

a gate insulating film formed over the semiconductor;

a gate electrode formed over ~~[[a]]~~ the gate insulating film;

a hard mask formed over the gate electrode; and

an interlayer insulating film over the hard mask,

wherein the interlayer insulating film is in contact with at least a part of a lateral face of the gate electrode.

4. (Currently Amended) A semiconductor device, comprising:

a substrate having an insulating surface;

a semiconductor film over the substrate;

a gate insulating film formed over the semiconductor;

a gate electrode formed over ~~[[a]]~~ the gate insulating film;

a hard mask formed over the gate electrode;

an interlayer insulating film over the hard mask; and

a conductive film which is in contact with the gate electrode,

wherein the interlayer insulating film is in contact with at least a part of a lateral face of the gate electrode, and

wherein the conductive film is to serve as a wire for sending a signal to the gate electrode or as a connection layer for connecting a wire with the gate electrode.

5-8. (Canceled)

9. (Original) A semiconductor device, according to claim 3, wherein the gate electrode is selected from the group consisting of tantalum nitride and tungsten.

10. (Original) A semiconductor device, according to claim 3, wherein the hard mask is selected from the group consisting of silicon oxide.

11. (Original) A semiconductor device, according to claim 4, wherein the gate electrode is selected from the group consisting of tantalum nitride and tungsten.

12. (Original) A semiconductor device, according to claim 4, wherein the hard mask is selected from the group consisting of silicon oxide.

13. (Original) A semiconductor device, according to claim 4, wherein the conductive film is selected from the group consisting of tantalum nitride and tungsten.

14. (Currently Amended) A semiconductor device, comprising:
a substrate having an insulating surface;
a semiconductor film over the substrate;
a gate insulating film formed over the semiconductor;
a gate electrode formed over ~~[[a]]~~ the gate insulating film; and
an island shaped hard mask formed over the gate electrode,
wherein side walls of the island shaped hard mask have an angle of inclination of 0° or more, and of 90° or less.

15. (Currently Amended) A semiconductor device, comprising:
a substrate having an insulating surface;
a semiconductor film over the substrate;
a gate insulating film formed over the semiconductor;
a gate electrode formed over ~~[[a]]~~ the gate insulating film; and
an island shaped hard mask formed over the gate electrode,
wherein side walls of the island shaped hard mask forms arc shapes.

16. (Previously Presented) A semiconductor device, according to claim 14, wherein the angle is inclination of 35° or more, and 50° or less.

17. (Previously Presented) A semiconductor device, according to claim 14, wherein the gate electrode is selected from the group consisting of tantalum nitride and tungsten.

18. (Previously Presented) A semiconductor device, according to claim 14, wherein the island shaped hard mask is selected from the group consisting of silicon oxide.

19. (Previously Presented) A semiconductor device, according to claim 15, wherein the gate electrode is selected from the group consisting of tantalum nitride and tungsten.

20. (Previously Presented) A semiconductor device, according to claim 15, wherein the island shaped hard mask is selected from the group consisting of silicon oxide.

21. (Currently Amended) A semiconductor device, comprising:
a substrate having an insulating surface;
a semiconductor film over the substrate;
a gate insulating film formed over the semiconductor;
a gate electrode formed over [[a]] the gate insulating film;
an island shaped hard mask formed over the gate electrode; and
a conductive film which is in contact with the gate electrode,
wherein the conductive film is to serve as a wire for sending a signal to the gate electrode or as a connection layer for connecting a wire with the gate electrode, and
wherein side walls of the island shaped hard mask have an angle of inclination of 0° or more, and of 90° or less.

22. (Currently Amended) A semiconductor device, comprising:
a substrate having an insulating surface;
a semiconductor film over the substrate;
a gate insulating film formed over the semiconductor;
a gate electrode formed over [[a]] the gate insulating film;
an island shaped hard mask formed over the gate electrode; and

a conductive film which is in contact with the gate electrode,
wherein the conductive film is to serve as a wire for sending a signal to the gate electrode or as a connection layer for connecting a wire with the gate electrode, and
wherein side walls of the island shaped hard mask forms arc shapes.

23. (Previously Presented) A semiconductor device, according to claim 21, wherein the angle is inclination of 35° or more, and 50° or less.

24. (Previously Presented) A semiconductor device, according to claim 21, wherein the gate electrode is selected from the group consisting of tantalum nitride and tungsten.

25. (Previously Presented) A semiconductor device, according to claim 21, wherein the island shaped hard mask is selected from the group consisting of silicon oxide.

26. (Previously Presented) A semiconductor device, according to claim 22, wherein the gate electrode is selected from the group consisting of tantalum nitride and tungsten.

27. (Previously Presented) A semiconductor device, according to claim 22, wherein the island shaped hard mask is selected from the group consisting of silicon oxide.

28. (New) A semiconductor device, comprising:
a substrate having an insulating surface;
a semiconductor film over the substrate;
a gate insulating film formed over the semiconductor;
a gate electrode formed over the gate insulating film; and
a hard mask formed on and in contact with the gate electrode,
wherein the gate electrode is formed by etching using the hard mask as a mask.

29. (New) A semiconductor device, comprising:
a substrate having an insulating surface;
a semiconductor film over the substrate;

a gate insulating film formed over the semiconductor;
a gate electrode formed over the gate insulating film;
a hard mask formed on and in contact with the gate electrode; and
a conductive film formed in contact with the gate electrode,
wherein the conductive film at least partly overlaps the gate electrode, and
wherein the gate electrode is formed by etching using the hard mask and the
conductive film as a mask.

30. (New) A semiconductor device according to claim 28,
wherein the semiconductor device further comprising an interlayer insulating film over
the hard mask, and
wherein the interlayer insulating film is in contact with the gate insulating film.

31. (New) A semiconductor device according to claim 28, wherein the hard mask is
not in contact with the gate insulating film.

32. (New) A semiconductor device, according to claim 28, wherein the gate electrode
is selected from the group consisting of tantalum nitride and tungsten.

33. (New) A semiconductor device, according to claim 28, wherein the hard mask is
selected from the group consisting of silicon oxide.

34. (New) A semiconductor device according to claim 29,
wherein the semiconductor device further comprising an interlayer insulating film over
the hard mask, and
wherein the interlayer insulating film is in contact with the gate insulating film.

35. (New) A semiconductor device according to claim 29, wherein the hard mask is
not in contact with the gate insulating film.

36. (New) A semiconductor device, according to claim 29, wherein the gate electrode

is selected from the group consisting of tantalum nitride and tungsten.

37. (New) A semiconductor device, according to claim 29, wherein the hard mask is selected from the group consisting of silicon oxide.

38. (New) A semiconductor device, according to claim 29, wherein the conductive film is selected from the group consisting of tantalum nitride and tungsten.